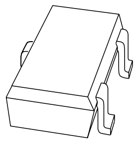

BAS21W series

High-voltage switching diodes

Rev. 01 — 9 October 2009 Product data sheet

1. Product profile

1.1 General description

High-voltage switching diodes, encapsulated in a very small Surface-Mounted Device (SMD) plastic package.

Table 1. Product overview

Type number	Configuration	Package		Package configuration
		NXP	JEDEC	
BAS21W	single	SOT323	SC-70	very small
BAS21AW	dual common anode			
BAS21SW	dual series			

1.2 Features

- High switching speed: $t_{rr} \leq 50$ ns
- Low leakage current
- High reverse voltage: $V_R \leq 250$ V
- Low capacitance: $C_d \leq 2$ pF
- Very small SMD plastic package
- AEC-Q101 qualified

1.3 Applications

- High-speed switching
- General-purpose switching
- Voltage clamping
- Reverse polarity protection

1.4 Quick reference data

Table 2. Quick reference data

Symbol	Parameter	Conditions		Min	Typ	Max	Unit
Per diode							
I_F	forward current		[1]	-	-	225	mA
I_R	reverse current	V_R = 200 V		-	-	100	nA
V_R	reverse voltage			-	-	250	V
t_{rr}	reverse recovery time		[2]	-	-	50	ns

[1] Single diode loaded.

[2] When switched from I_F = 10 mA to I_R = 10 mA; R_L = 100 Ω; measured at I_R = 1 mA.

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2. Pinning information

Table 3. Pinning

Pin	Description	Simplified outline	Graphic symbol
BAS21W			
1	anode		
2	not connected		
3	cathode		
BAS21AW			
1	cathode (diode 1)		
2	cathode (diode 2)		
3	common anode		
BAS21SW			
1	anode (diode 1)		
2	cathode (diode 2)		
3	cathode (diode 1), anode (diode 2)		

3. Ordering information

Table 4. Ordering information

Type number	Package		
	Name	Description	Version
BAS21W	SC-70	plastic surface-mounted package; 3 leads	SOT323
BAS21AW			
BAS21SW			

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4. Marking

Table 5. Marking codes

Type number	Marking code[1]
BAS21W	X4*
BAS21AW	X6*
BAS21SW	X5*

[1] * = -: made in Hong Kong
* = p: made in Hong Kong
* = t: made in Malaysia
* = W: made in China

5. Limiting values

Table 6. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
Per diode						
V_R	reverse voltage			-	250	V
I_F	forward current		[1]	-	225	mA
			[2]	-	125	mA
I_{FRM}	repetitive peak forward current			-	625	mA
I_{FSM}	non-repetitive peak forward current	square wave	[3]			
		t_p = 1 µs		-	9	A
		t_p = 100 µs		-	3	A
		t_p = 10 ms		-	1.7	A
Per device						
P_{tot}	total power dissipation	$T_{amb} \leq 25$ °C	[4]	-	200	mW
T_j	junction temperature			-	150	°C
T_{amb}	ambient temperature			–55	+150	°C
T_{stg}	storage temperature			–65	+150	°C

[1] Single diode loaded.

[2] Double diode loaded.

[3] T_j = 25 °C prior to surge.

[4] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.

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6. Thermal characteristics

Table 7. Thermal characteristics

Symbol	Parameter	Conditions		Min	Typ	Max	Unit
Per device							
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air	[1]	-	-	625	K/W
$R_{th(j-sp)}$	thermal resistance from junction to solder point			-	-	300	K/W

[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

7. Characteristics

Table 8. Characteristics

T_{amb} = 25 °C unless otherwise specified.

Symbol	Parameter	Conditions		Min	Typ	Max	Unit
Per diode							
V_F	forward voltage	I_F = 100 mA		-	-	1.0	V
		I_F = 200 mA		-	-	1.25	V
I_R	reverse current	V_R = 200 V		-	-	100	nA
		V_R = 200 V; T_j = 150 °C		-	-	100	µA
C_d	diode capacitance	f = 1 MHz; V_R = 0 V		-	-	2	pF
t_{rr}	reverse recovery time		[1]	-	-	50	ns

[1] When switched from I_F = 10 mA to I_R = 10 mA; R_L = 100 Ω; measured at I_R = 1 mA.

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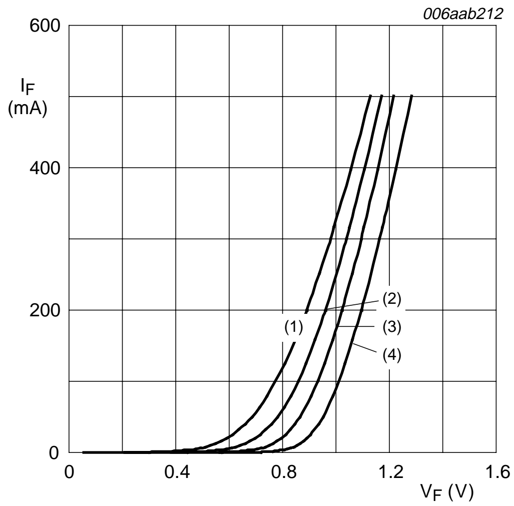
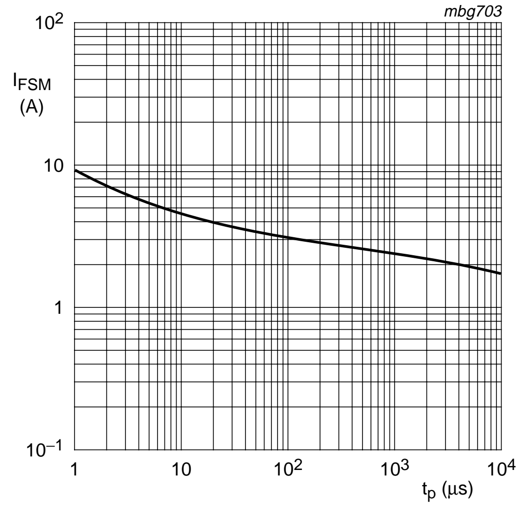


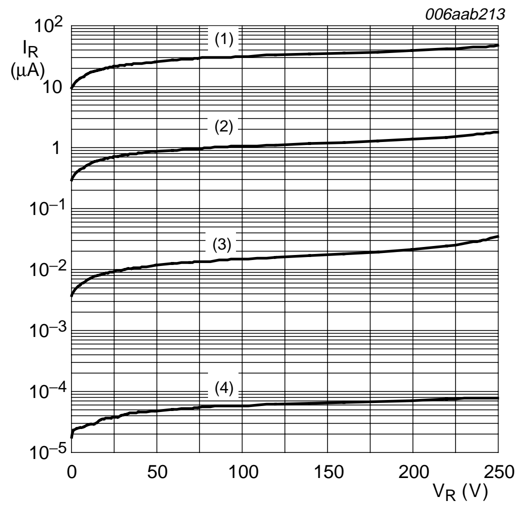
(1) T_{amb} = 150 °C
(2) T_{amb} = 85 °C
(3) T_{amb} = 25 °C
(4) T_{amb} = −40 °C

Fig 1. Forward current as a function of forward voltage; typical values



Based on square wave currents.
T_j = 25 °C; prior to surge

Fig 2. Non-repetitive peak forward current as a function of pulse duration; maximum values



(1) T_{amb} = 150 °C
(2) T_{amb} = 85 °C
(3) T_{amb} = 25 °C
(4) T_{amb} = −40 °C

Fig 3. Reverse current as a function of reverse voltage; typical values

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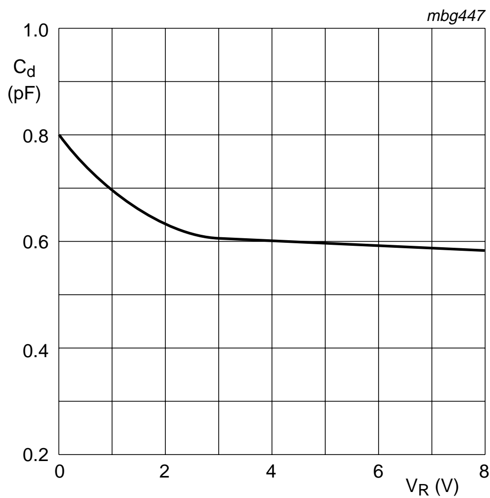
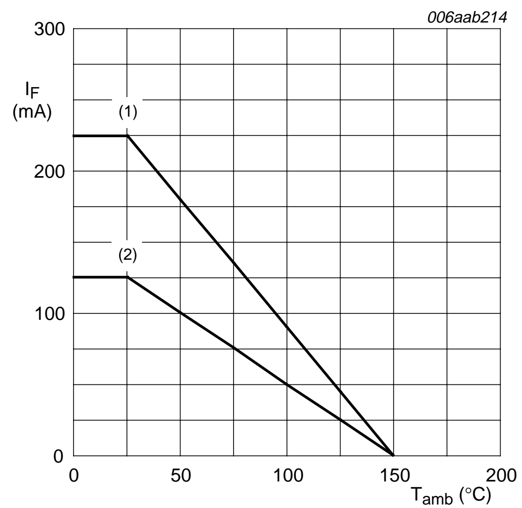


f = 1 MHz; T_{amb} = 25 °C

Fig 4. Diode capacitance as a function of reverse voltage; typical values



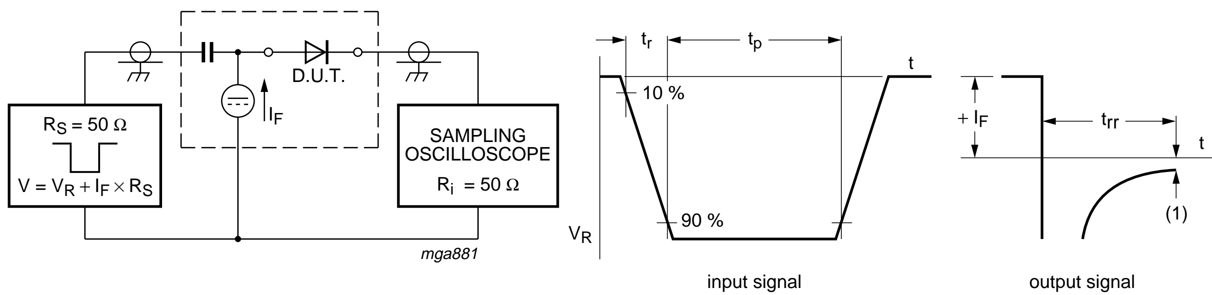
FR4 PCB, standard footprint

(1) Single diode loaded.

(2) Double diode loaded.

Fig 5. Forward current as a function of ambient temperature; derating curve

8. Test information



(1) I_R = 1 mA

Fig 6. Reverse recovery time test circuit and waveforms

8.1 Quality information

This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard *Q101 - Stress test qualification for discrete semiconductors*, and is suitable for use in automotive applications.

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9. Package outline

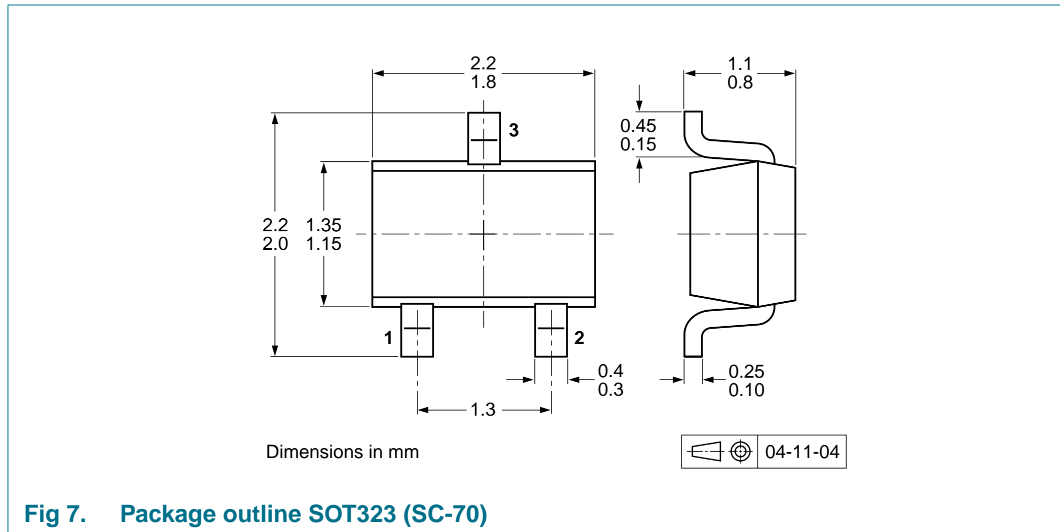

Fig 7. Package outline SOT323 (SC-70)

10. Packing information

Table 9. Packing methods

The indicated -xxx are the last three digits of the 12NC ordering code.[1]

Type number	Package	Description	Packing quantity	
			3000	10000
BAS21W	SOT323	4 mm pitch, 8 mm tape and reel	-115	-135
BAS21AW				
BAS21SW				

[1] For further information and the availability of packing methods, see Section 14.

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11. Soldering

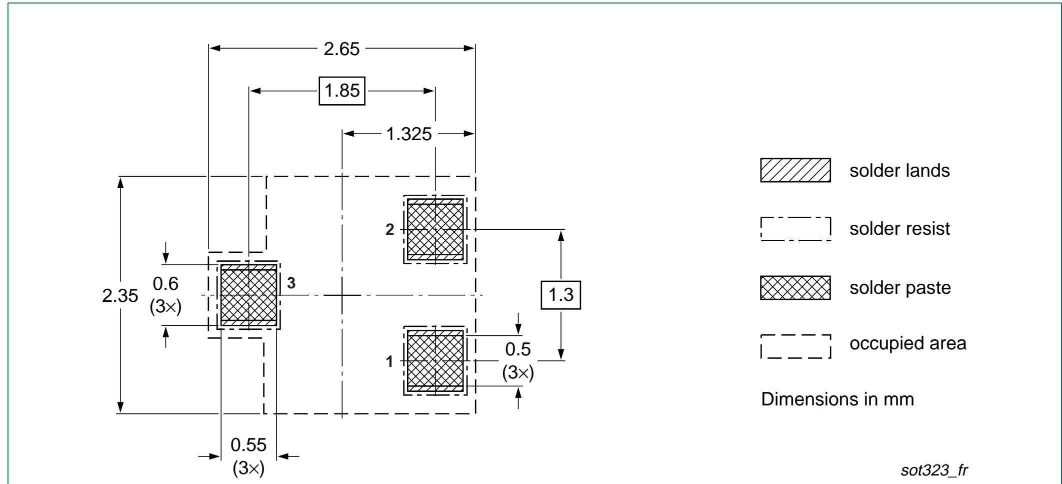

Fig 8. Reflow soldering footprint SOT323 (SC-70)

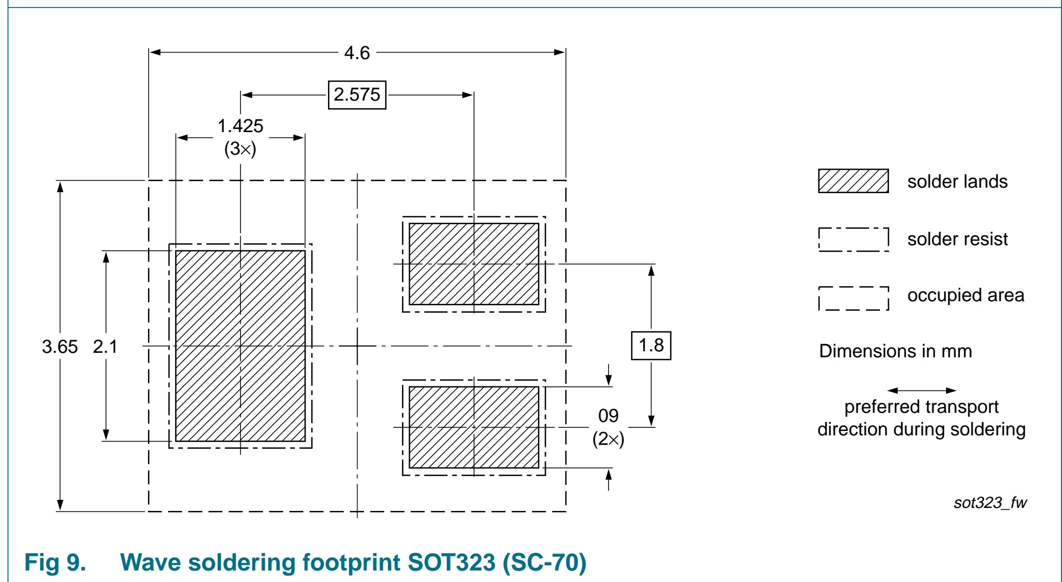

Fig 9. Wave soldering footprint SOT323 (SC-70)

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12. Revision history

Table 10. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
BAS21W_SER_1	20091009	Product data sheet	-	-

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13. Legal information

13.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

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15. Contents

1 **Product profile** 1
1.1 General description. 1
1.2 Features 1
1.3 Applications 1
1.4 Quick reference data. 1
2 **Pinning information** 2
3 **Ordering information** 2
4 **Marking** 3
5 **Limiting values** 3
6 **Thermal characteristics** 4
7 **Characteristics** 4
8 **Test information** 6
8.1 Quality information 6
9 **Package outline** 7
10 **Packing information** 7
11 **Soldering** 8
12 **Revision history** 9
13 **Legal information** 10
13.1 Data sheet status 10
13.2 Definitions 10
13.3 Disclaimers 10
13.4 Trademarks 10
14 **Contact information** 10
15 **Contents** 11

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